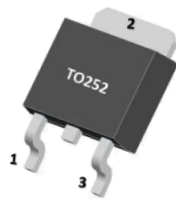


■ DESCRIPTION

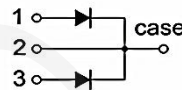
The MBR20100CT meet the ROHS and Green Product requirement with full function reliability approved.

■ FEATURE

- *Schottky Barrier Chip
- *Guard Ring Die Construction for Transient Protection
- *Low Power Loss,High Efficiency
- *High Surge Capability
- *High Current Capability and Low Forward Voltage Drop
- *For Use in Low Voltage, High Frequency Inverters,Free Wheeling, and Polarity Protection Applications



- 1. ANODE
- 2. CATHODE
- 3. ANODE



■ ABSOLUTE MAXIMUM RATINGS(TA=25°C, unless otherwise specified.)

SYMBOL	PARAMETER	VALUE	UNIT
VRRM	Peak repetitive reverse voltage	100	V
VRWM	Working peak reverse voltage	100	V
VR	DC blocking voltage	100	V
VR(RMS)	RMS reverse voltage	70	V
IO	Average rectified output current	20 (10*2)	A
IFSM	Non-Repetitive peak forward surge current	150*2	A
Tj	Junction temperature	175	°C
Tstg	Storage temperature	-55 ~ +150	°C
Cj (Ctot)	Typical total capacitance VR=5V,f=1MHz	500	pF
RθJA	Thermal Resistance from Junction to Ambient	100	°C/W
RθJC	Thermal Resistance From Junction To Case	5	°C/W

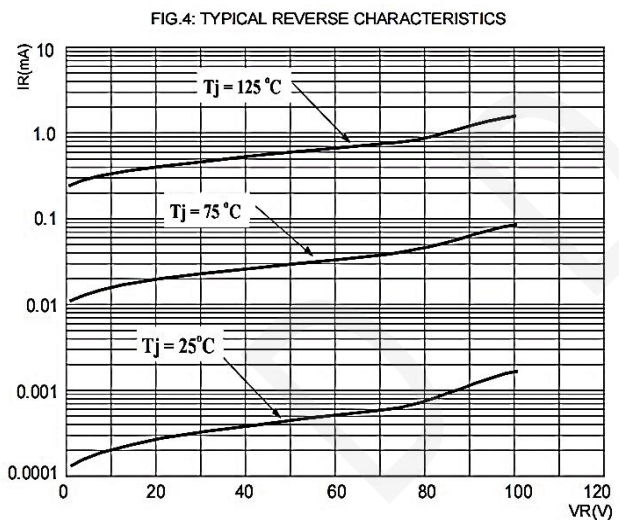
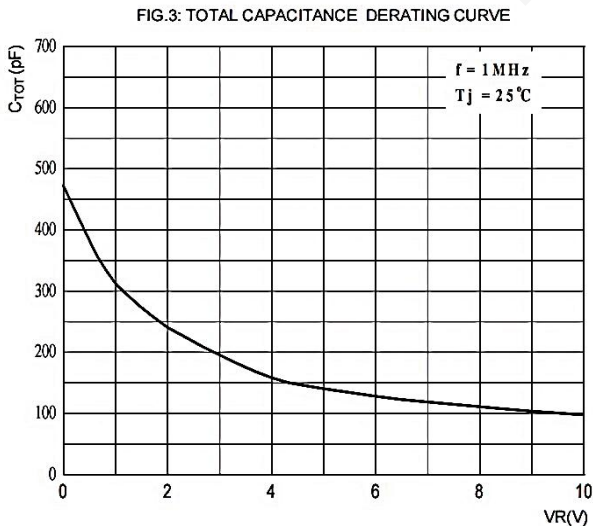
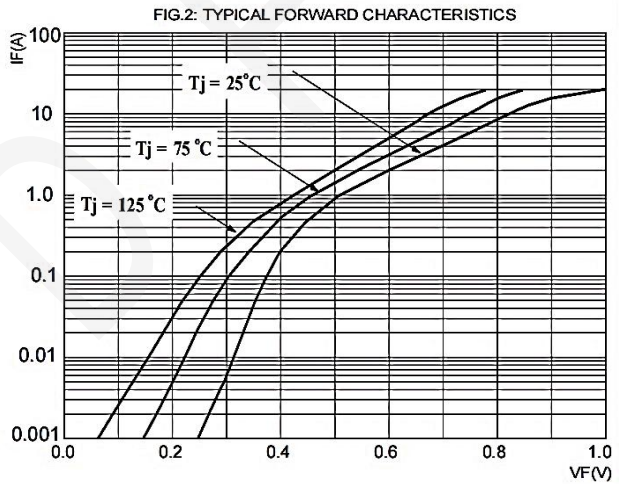
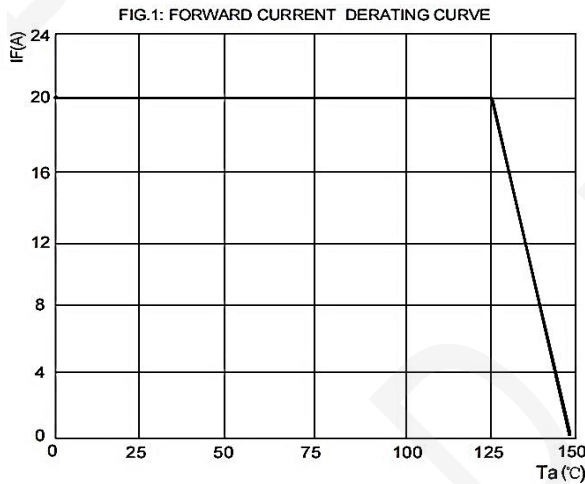
Notes: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (TA=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Reverse voltage	$V_{(BR)}$	$I_R=0.2mA$	100			V
Reverse current	I_R	$V_R=100V$	$T_j = 25^\circ C$	1	5	μA
			$T_j = 125^\circ C$	5.0		mA
Forward voltage	V_F	$I_F=5A$	$T_j = 25^\circ C$	0.72		V
			$T_j = 125^\circ C$	0.60		V
		$I_F=10A$	$T_j = 25^\circ C$	0.82	0.86	V
			$T_j = 125^\circ C$	0.68		V

*Pulse test: pulse width $\leq 300\mu s$, duty cycle $\leq 2.0\%$

■ TYPICAL CHARACTERISTICS



TO - 252 Package Outline Dimensions

